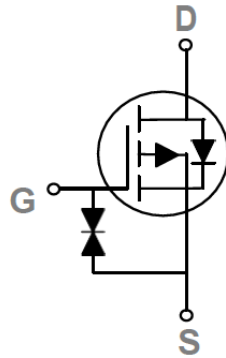
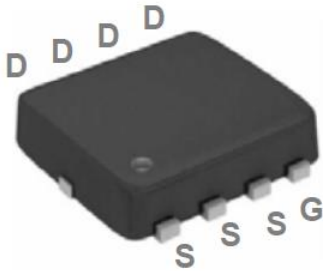


General Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

DFN3x3 Pin Configuration



BVDSS	RDSON	ID
-30V	20mΩ	-30A

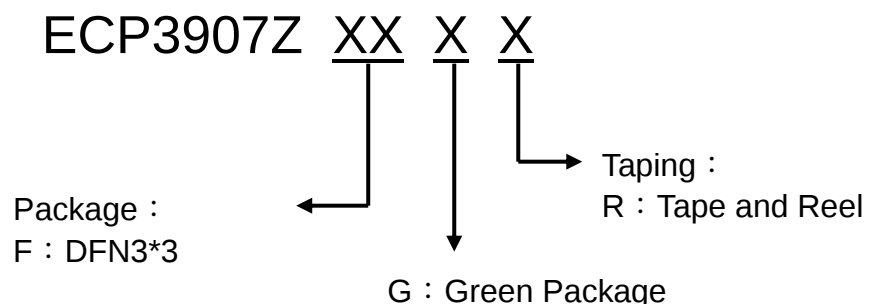
Features

- ◆ -30V, -30A, $R_{DS(ON)} = 20\text{m}\Omega @ V_{GS} = -10\text{V}$
- ◆ Fast switching
- ◆ Green Device Available
- ◆ Suit for -4.5V Gate Drive Applications
- ◆ ESD Protection Embedded

Application

- ◆ MB / VGA / Vcore
- ◆ POL Applications
- ◆ Load Switch
- ◆ LED Application

Ordering Information



**Absolute Maximum Ratings** $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_C=25^{\circ}\text{C}$)	-30	A
	Drain Current – Continuous ($T_C=100^{\circ}\text{C}$)	-19	A
I_{DM}	Drain Current – Pulsed ¹	-120	A
P_D	Power Dissipation ($T_C=25^{\circ}\text{C}$)	27	W
	Power Dissipation – Derate above 25°C	0.22	W/ $^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	4.6	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics $T_J=25^{\circ}\text{C}$, unless otherwise noted**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=-250\mu\text{A}$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.03	---	V/ $^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-27\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
		$V_{DS}=-24\text{V}$, $V_{GS}=0\text{V}$, $T_J=125^{\circ}\text{C}$	---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	---	---	± 10	μA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-8\text{A}$	---	16	20	m
		$V_{GS}=-4.5\text{V}$, $I_D=-6\text{A}$	---	26	35	m
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu\text{A}$	-1.2	-1.6	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4	---	mV/ $^{\circ}\text{C}$
gfs	Forward Transconductance	$V_{DS}=-10\text{V}$, $I_D=-8\text{A}$	---	6.8	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{2, 3}	$V_{DS}=-15\text{V}$, $V_{GS}=-4.5\text{V}$, $I_D=-5\text{A}$	---	11	17	nC
Q_{gs}	Gate-Source Charge ^{2, 3}		---	3.4	6	
Q_{gd}	Gate-Drain Charge ^{2, 3}		---	4.2	8	
$T_{d(on)}$	Turn-On Delay Time ^{2, 3}	$V_{DD}=-15\text{V}$, $V_{GS}=-10\text{V}$, $R_G=6\Omega$ $I_D=-1\text{A}$	---	5.8	11	ns
T_r	Rise Time ^{2, 3}		---	18.8	36	
$T_{d(off)}$	Turn-Off Delay Time ^{2, 3}		---	46.9	90	
T_f	Fall Time ^{2, 3}		---	12.3	23	
C_{iss}	Input Capacitance	$V_{DS}=-15\text{V}$, $V_{GS}=0\text{V}$, $F=1\text{MHz}$	---	1250	2500	pF
C_{oss}	Output Capacitance		---	160	320	
$Crss$	Reverse Transfer Capacitance		---	90	180	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-30	A
I_{SM}	Pulsed Source Current		---	---	-60	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ C$	---	---	-1	V

Note :

- 1.Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 3.Essentially independent of operating temperature.

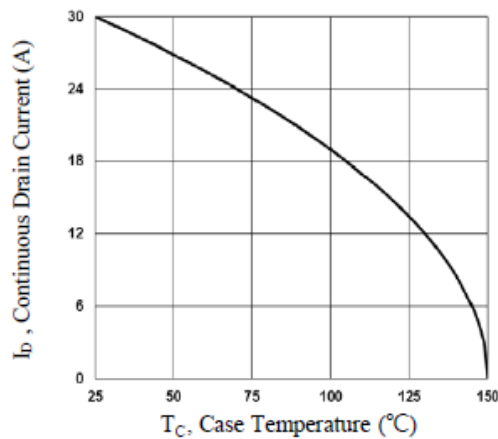


Fig.1 Continuous Drain Current vs. T_C

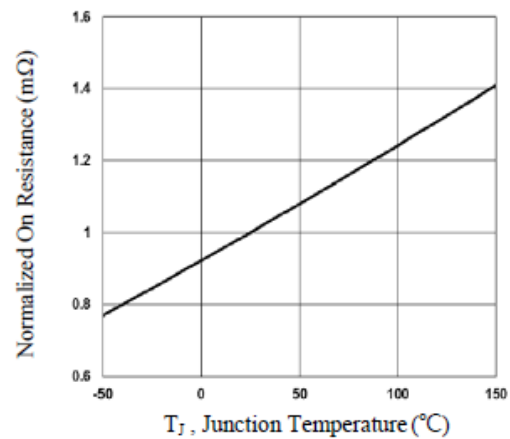


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

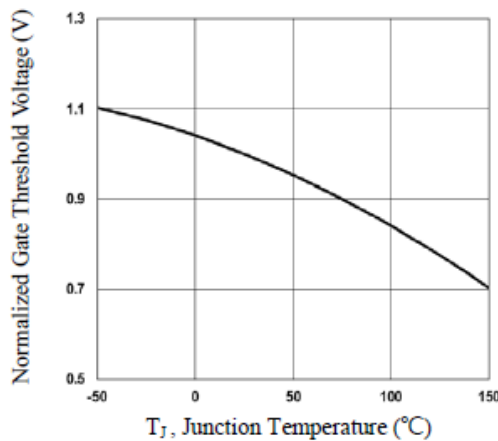


Fig.3 Normalized V_{th} vs. T_J

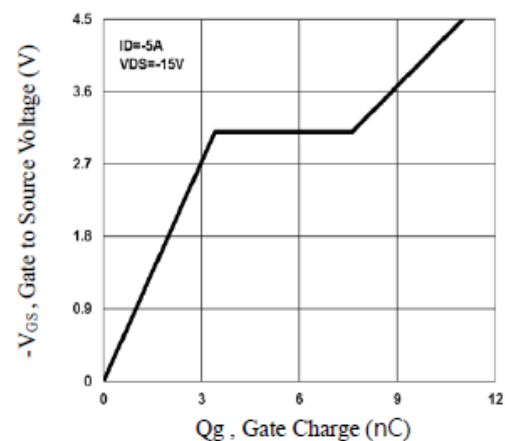


Fig.4 Gate Charge Waveform

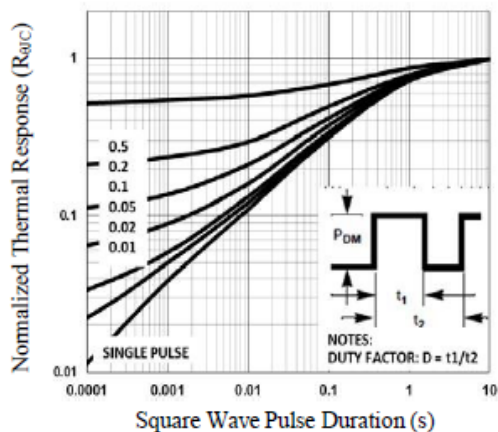


Fig.5 Normalized Transient Impedance

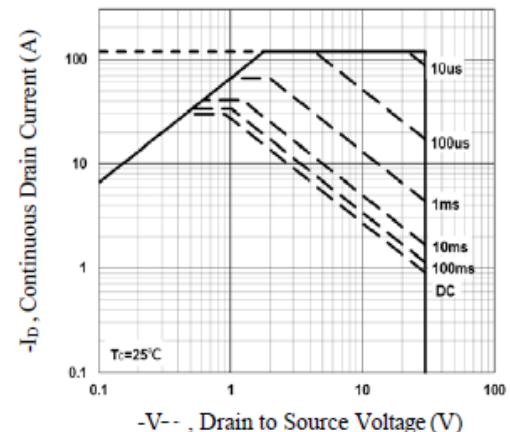


Fig.6 Maximum Safe Operation Area

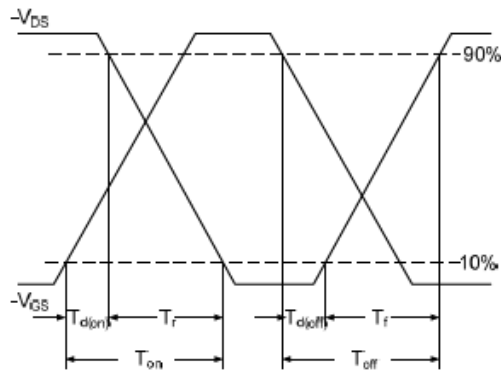


Fig.7 Switching Time Waveform

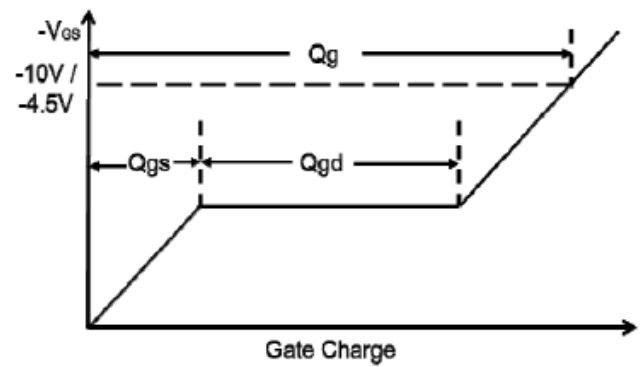
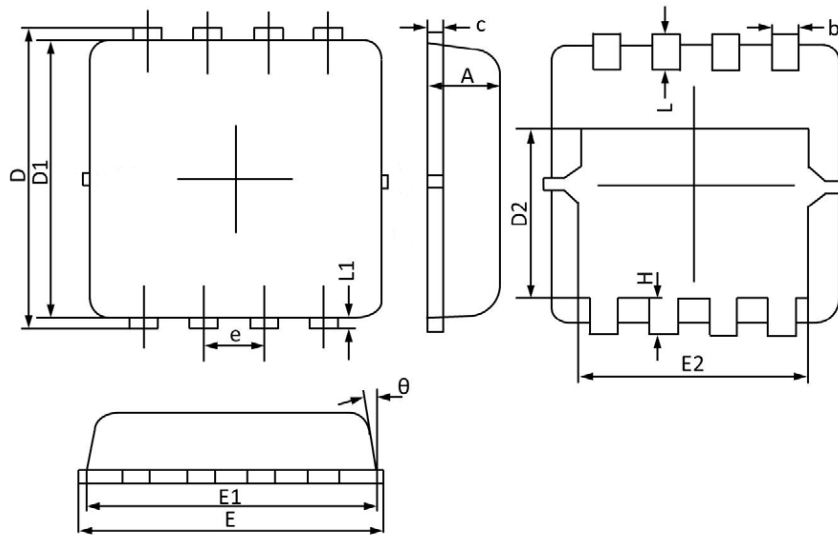


Fig.8 Gate Charge Waveform

DFN3x3 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	0.900	0.700	0.035	0.028
b	0.350	0.240	0.014	0.009
c	0.250	0.100	0.010	0.004
D	3.450	3.050	0.136	0.120
D1	3.200	2.900	0.126	0.114
D2	1.850	1.350	0.073	0.053
E	3.400	3.000	0.134	0.118
E1	3.250	2.900	0.128	0.114
E2	2.600	2.350	0.102	0.093
e	0.65BSC		0.026BSC	
H	0.500	0.300	0.020	0.012
L	0.500	0.300	0.020	0.012
L1	0.200	0.070	0.008	0.003
θ	12°	0°	12°	0°